

HIGH EFFICIENCY POWER RECTIFIER

DESCRIPTION: 1500 VOLT, 1.0 AMP ULTRA FAST RECTIFIER

FEATURES:

- **Single Chip Construction**
- **Hermetically Sealed**
- **Metallurgically Bonded**
- **Ultra Fast Recovery: 80 ns max @ 25°C**
- **Low Reverse Leakage Current**
- **For High Efficiency Applications**
- **TX, TXV and S-Level Screening Available**

MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at $T_A = 25^\circ\text{C}$ unless otherwise specified

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV)	-	-	-	1500	Vdc
Average DC Output Current (I_o)	$T_L = +75^\circ\text{C}$, $L = 0''$	-	-	1.0	Amps
Peak Single Cycle Surge Current (I_{FSM})	$t_p = 8.3$ ms Single Half Cycle Sine Wave, Superimposed On Rated Load	-	-	15	Amps(pk)
Operating and Storage Temp. (T_{OP} & T_{STG})	-	-65	-	+175	$^\circ\text{C}$
Breakdown Voltage (V_{BR})	$I_R = 50 \mu\text{A}$	1500			Vdc
Maximum Forward Voltage (V_F)	$I_F = 0.75$ A $I_F = 1.0$ A (300 μsec pulse, duty cycle < 2%)	-	-	2.5 3.0	Volts
Maximum Instantaneous Reverse Current At Rated PIV	$T_A = +25^\circ\text{C}$ $T_A = +125^\circ\text{C}$	-	-	2 100	μAmps
Reverse Recovery Time (t_{rr})	$I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $I_{RR}=0.25\text{A}$ $T_A = 25^\circ\text{C}$ $T_A = 100^\circ\text{C}$	-	-	80 250	nsec
Thermal Resistance ($R_{\theta JL}$, AXIAL) ($R_{\theta JEC}$, MELF)	Junction to Lead, $d = 0.375''$ Junction to End Caps	-	-	38 13	$^\circ\text{C/W}$

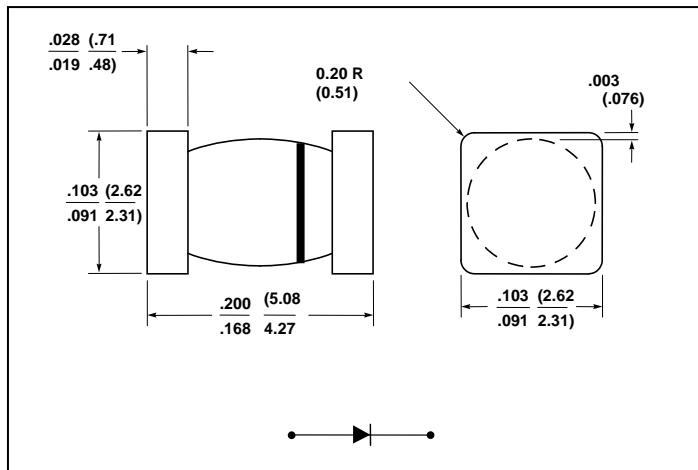
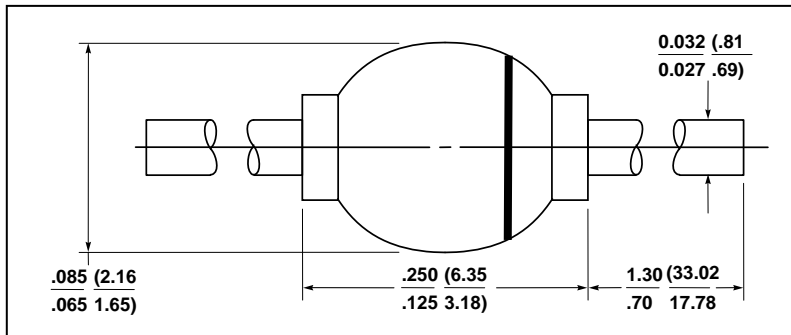
SENSITRON

SEMICONDUCTOR

SRS1150HE
SRS1150HEU

TECHNICAL DATA
DATA SHEET 5140, REV -

MECHANICAL DIMENSIONS In Inches / (mm), min./max.



NOTE: Cathode side of device is indicated by dark band marked on body.

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